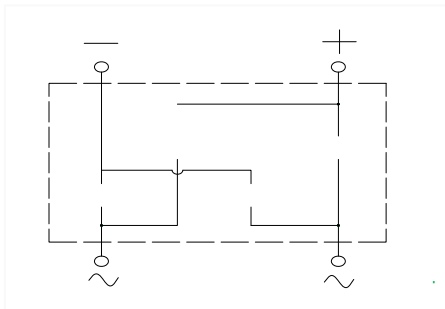


UL recognition, file #E313149
Glass passivated chip junction
Ideal for automated placement
High surge current capability
Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



General purpose use in AC/DC bridge full wave rectification for SMPS, lighting ballast, adapter, battery charger, home appliances, office equipment, and telecommunication applications.

: DBS

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, Halogen free

: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

As marked on body

($T_a=25$ Unless otherwise specified)

Device marking code			DB151S	DB152S	DB153S	DB154S	DB155S	DB156S	DB157S
Maximum Repetitive Peak Reverse Voltage	VRRM	V	50	100	200	400	600	800	1000
Maximum RMS Voltage	VRMS	V	35	70	140	280	420	560	700
Maximum DC blocking Voltage	VDC	V	50	100	200	400	600	800	1000
Average rectified output current @60Hz sine wave, R-load, $T_c=126$	I _O	A	1.5						
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, $T_j=25$	I _{FSM}	A	60						
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, $T_j=25$			120						
Current squared time @1ms $t \leq 8.3ms$ $T_j=25$, Rating of per diode	I ² t	A ² s	14.9						
Storage temperature	T _{stg}		-55 ~ +150						
Junction temperature	T _j		-55 ~ +150						

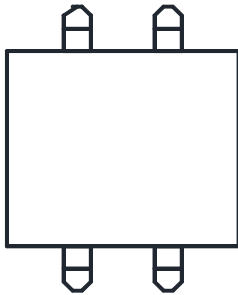
$T_a=25$ Unless otherwise specified

Maximum instantaneous forward voltage drop per diode	V _F	V	I _F M=0.7A	1.0					
Maximum DC reverse current at rated DC blocking voltage per diode	I _R	μA	T _j =25	5					
			T _j =125	100					
Typical junction capacitance	C _j	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	19					



$T_a=25$ Unless otherwise specified

Typical Thermal Resistance									
	R J-A								
	R J-L	/W				40.0			
						15.0	B	-	



Dim	Min	Max
A	6.20	6.50
B	9.60	10.30
C	5.00	5.20
D	8.13	8.51
E	2.80	3.30
F	1.02	1.2
G	0.22	0.33
H	1.02	1.53
I	0.076	0.33
J	1.80	2.10



Dimensions in millimeters

P1	8.73
P2	5.12
Q1	2.22
Q2	1.2

